

Application No. 09/916,682

Samples of Examples 1 to 8 were prepared as following: four kinds of heat generation patterns were formed on the ceramic substrate which is made of aluminum nitride or silicon carbide, with varying the curvatures of bending. Samples of Examples 9 to 16 were prepared as following: four kinds of heat generation patterns were formed inside the ceramic substrate which is made of aluminum nitride or silicon carbide, with varying the curvatures of bending.

Page 29, lines 12-24, delete current paragraph and insert therefor:

Samples of Comparative Examples 1 to 4 were prepared as following: heat generation patterns having a bending pattern of an approximate right angle as shown in Fig. 6 were formed on or inside the ceramic substrate which is made of aluminum nitride or silicon carbide. In addition, for other comparative examples, samples of Reference examples 1 to 4 were prepared as following: heat generation patterns having a bending pattern which describes an arc having a curvature radius of 25 mm were formed on or inside the ceramic substrate which is made of aluminum nitride or silicon carbide. Furthermore, samples of Reference examples 5 to 16 were prepared as following: heat generation patterns were formed on or inside the ceramic substrate which is made of alumina.

IN THE CLAIMS:

Please replace claims 1 and 2 as follows:

1. (Twice Amended) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and
a heat-generation pattern disposed on a surface of said disk-shaped ceramic substrate,

wherein said disk-shaped ceramic substrate has a diameter of 200 mm or more and said disk-shaped ceramic substrate is made of at least one selected from a group essentially consisting of nitride ceramics and carbide ceramics; and

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said heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 mm to 20 mm.

2. (Twice Amended) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and

a heat-generation pattern disposed within said disk-shaped ceramic substrate, wherein said disk-shaped ceramic substrate has a diameter of 200 mm or more and said disk-like ceramic substrate is made of at least one selected from a group essentially consisting of nitride ceramics and carbide ceramics; and

said heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 mm to 20 mm.

REMARKS

Claims 1-8 are pending. By this Amendment, the specification is amended to correct mistranslations of the Japanese language PCT Application No. PCT/JP00/05462. Claims 1 and 2 are amended to recite "a diameter of 200 mm or more" and to delete "a thickness of 18 mm or less." No new matter is added. Reconsideration of the application is respectfully solicited.

The attached Appendix includes marked-up copies of each rewritten paragraph (37 C.F.R. §1.121(b)(1)(iii)) and claim (37 C.F.R. §1.121(c)(1)(ii)).

Applicant respectfully submits that the application is in condition for allowance. Favorable reconsideration and prompt allowance of the claims are earnestly solicited.